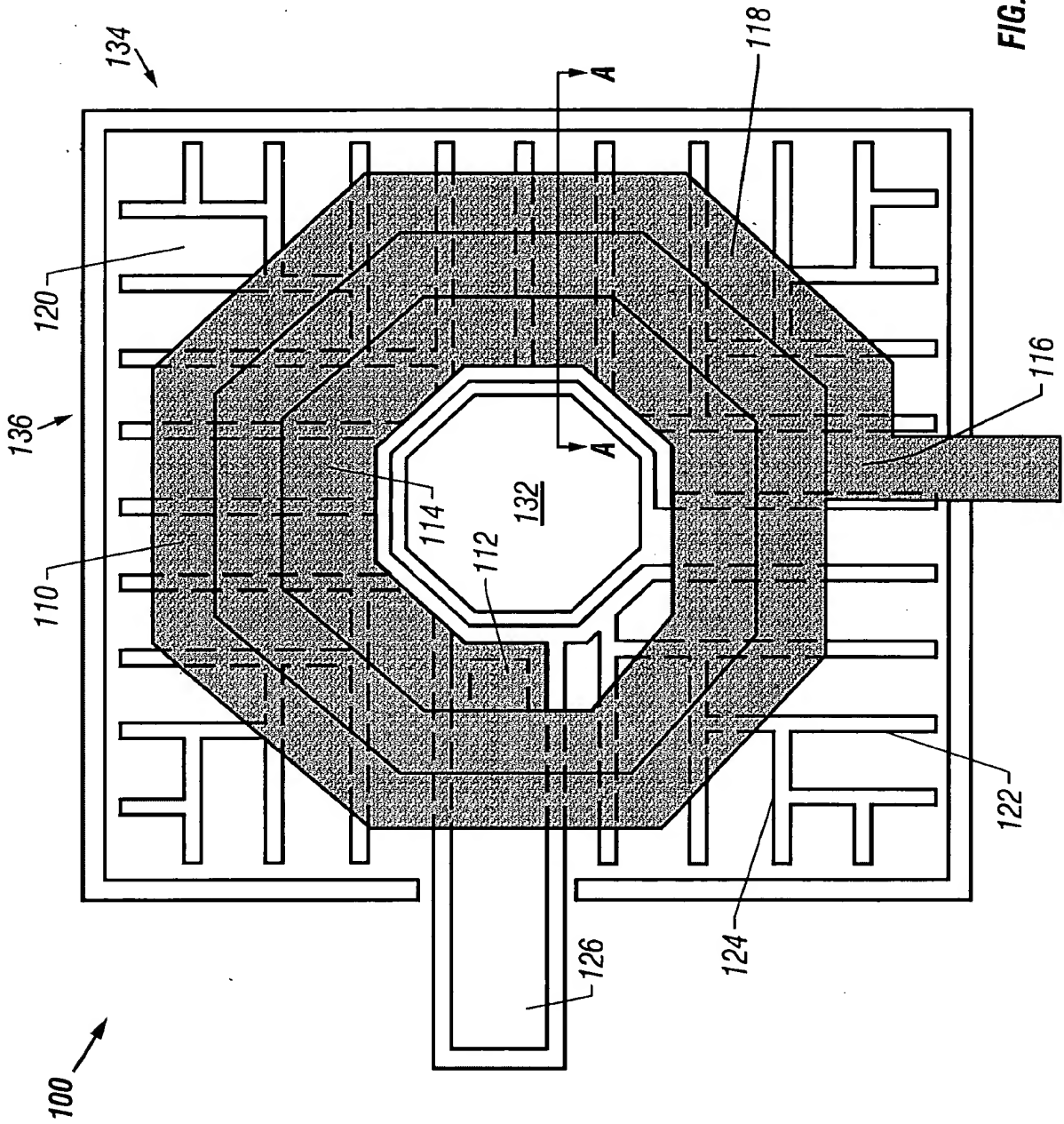


1/13



2/13

200 →

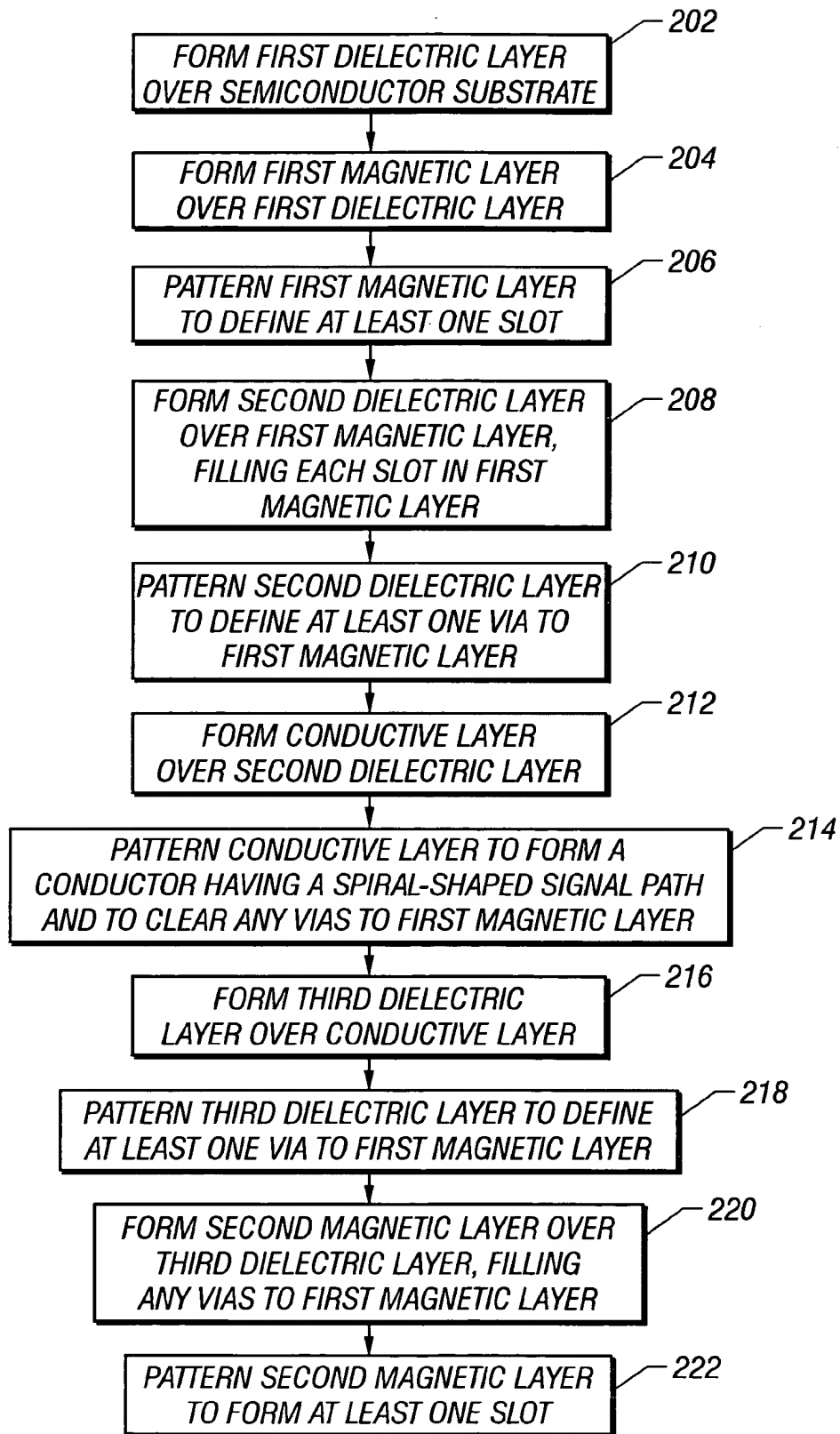


FIG. 2

3/13

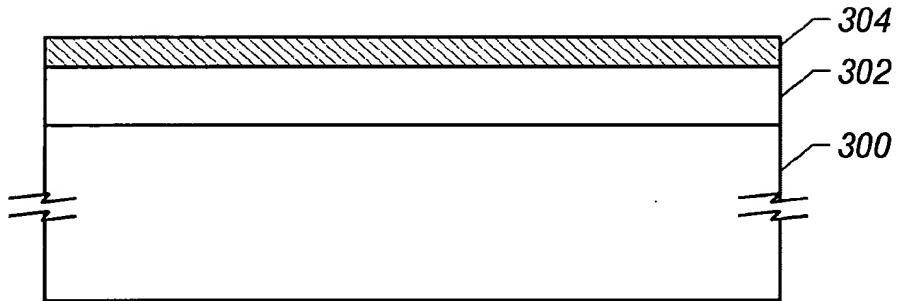


FIG. 3

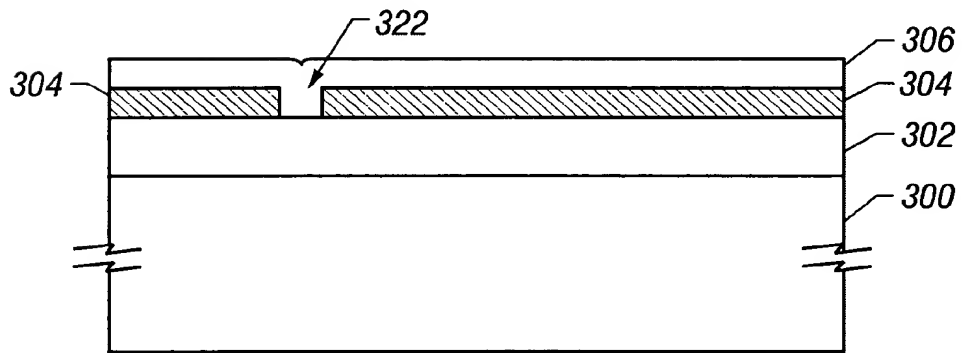


FIG. 4

09/853,370-0001

This cross-sectional view shows a semiconductor device. A substrate 300 is at the base, with a layer 302 above it. A gate stack is formed on top of layer 302, consisting of a gate dielectric 304 and a gate conductive layer 306. The gate conductive layer 306 has three rectangular regions 308. A conductive layer 310 is deposited over the gate stack. The conductive layer 310 has openings 322 that align with the gate conductive regions 308. The top surface of the conductive layer 310 is labeled 332, and the side surface is labeled 334.

FIG. 6

5/13

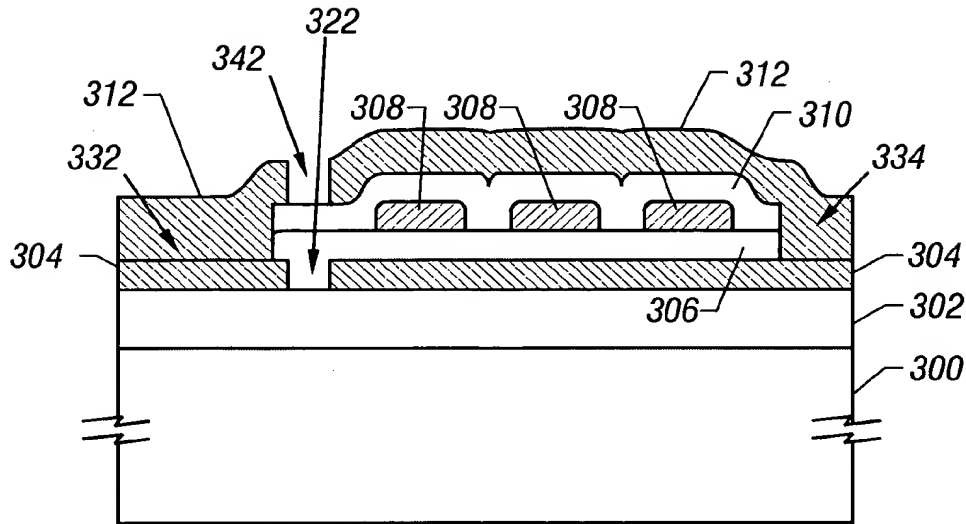


FIG. 7

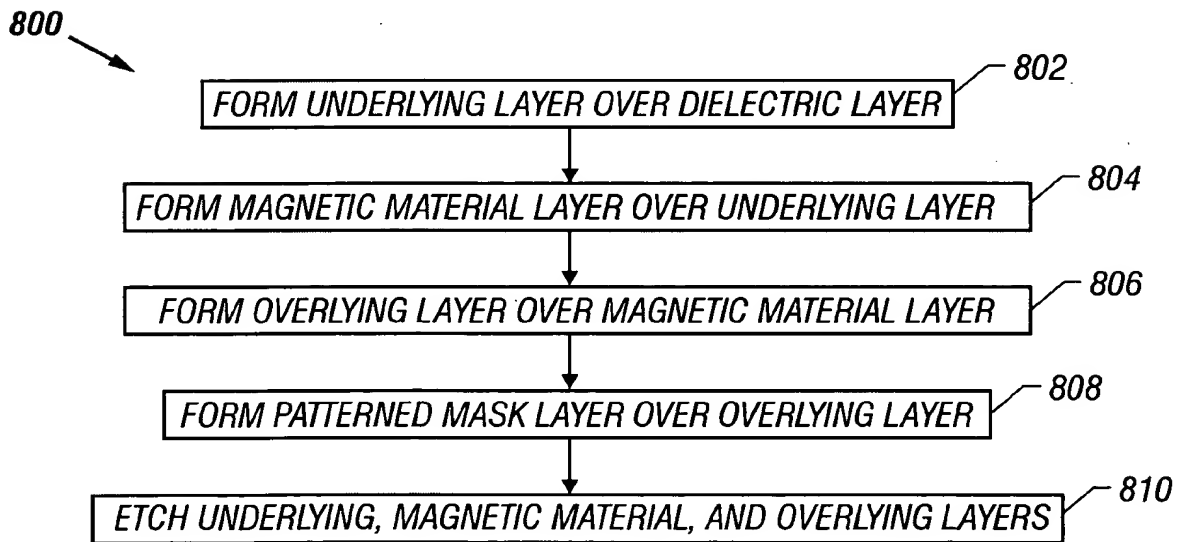


FIG. 8

6/13

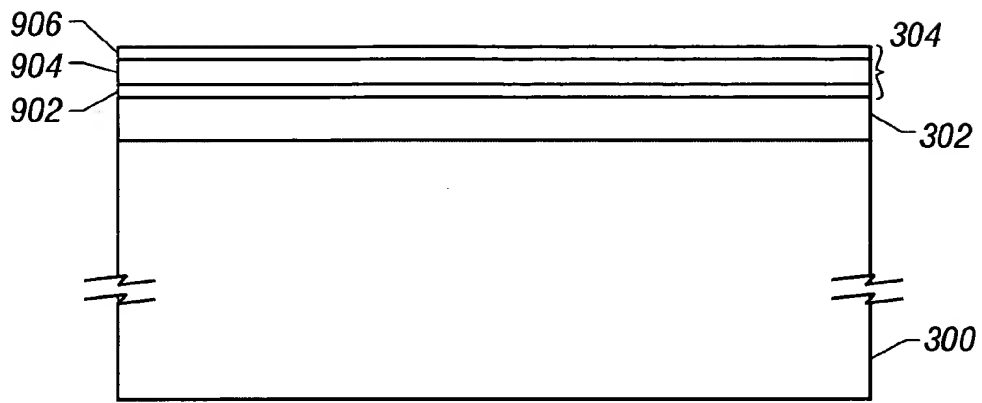


FIG. 9

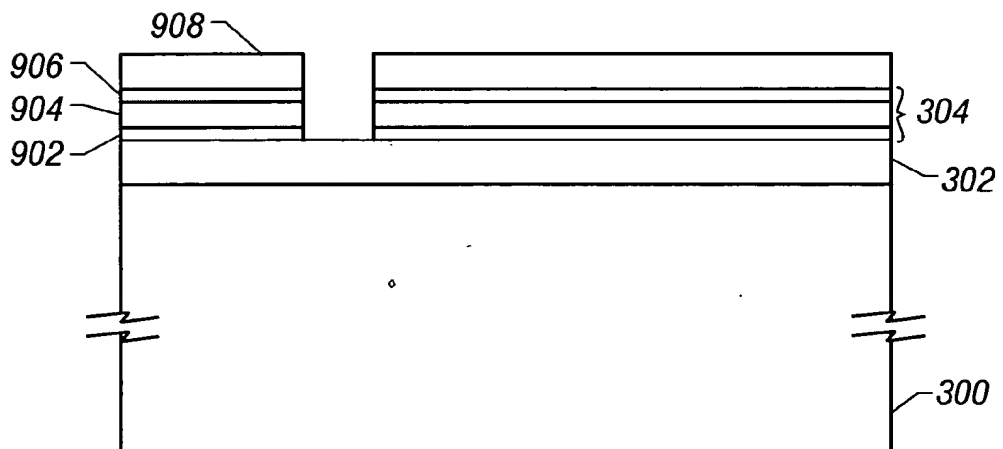


FIG. 10

7/13

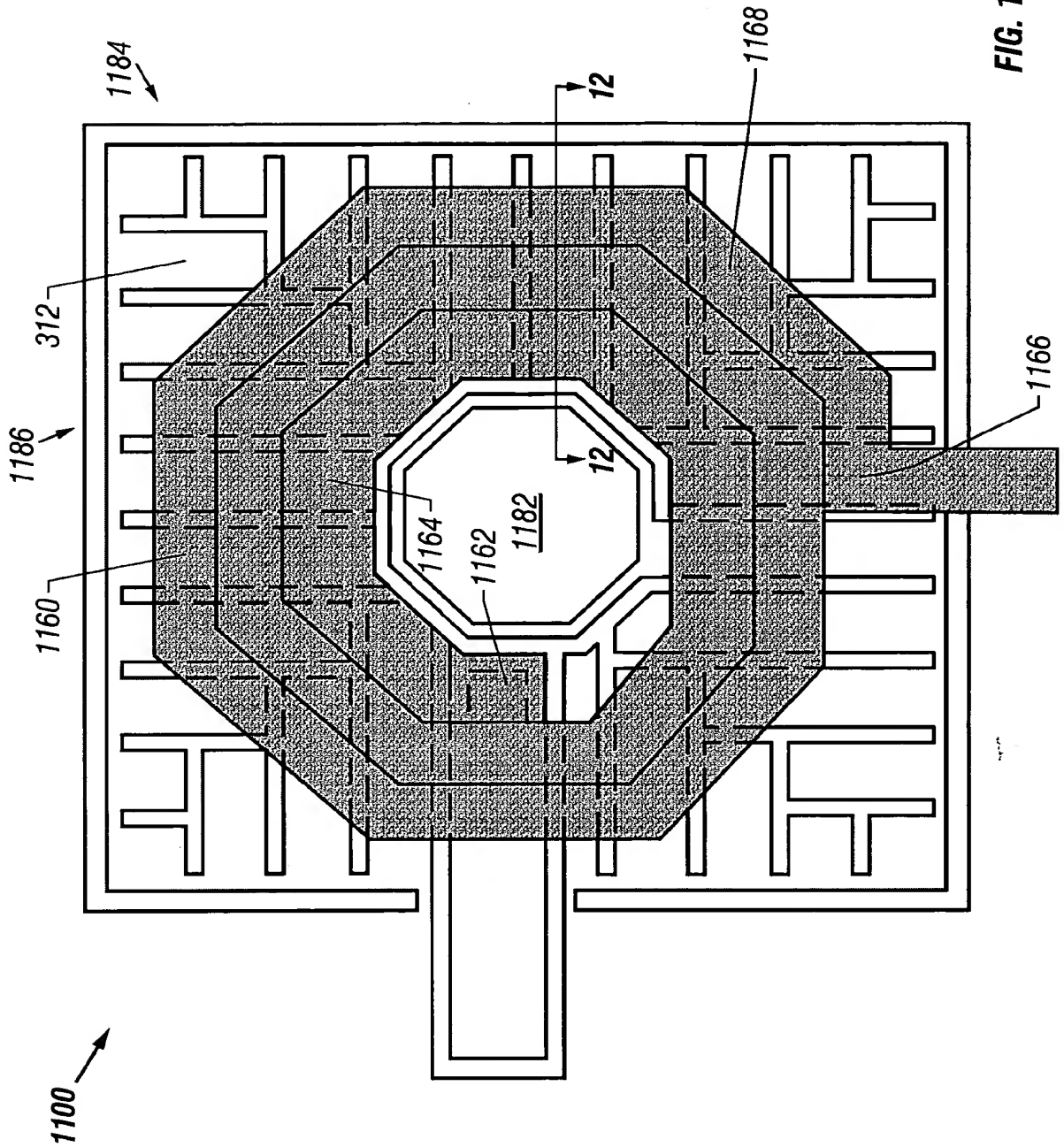


FIG. 11

8/13

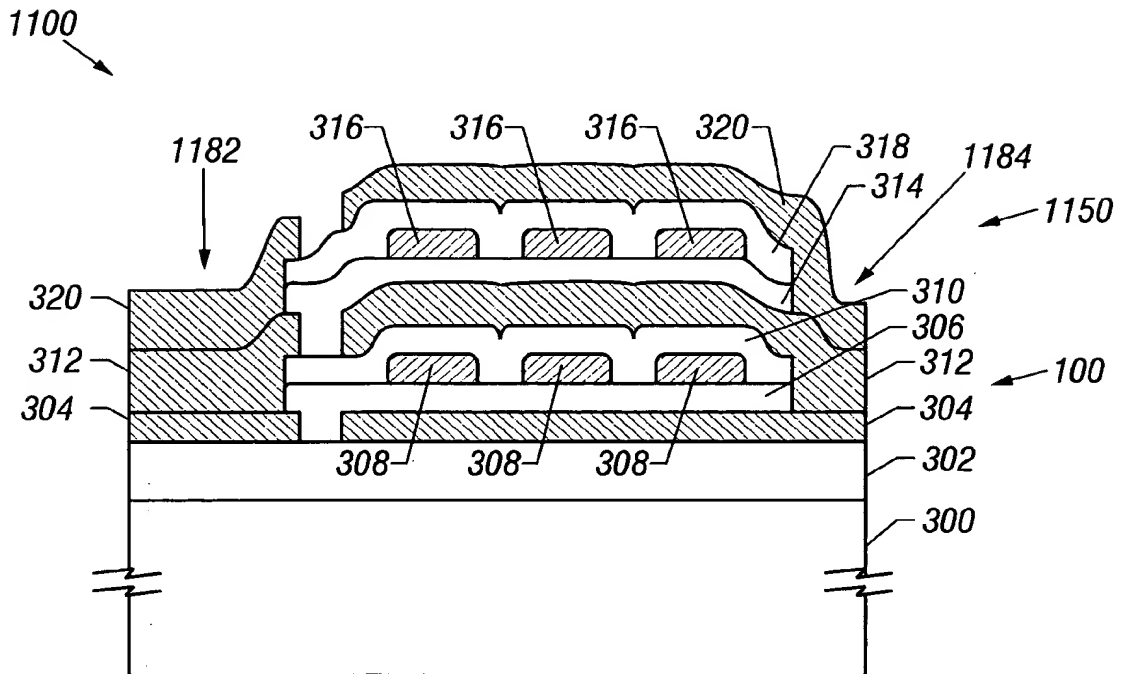


FIG. 12

10/13

1400

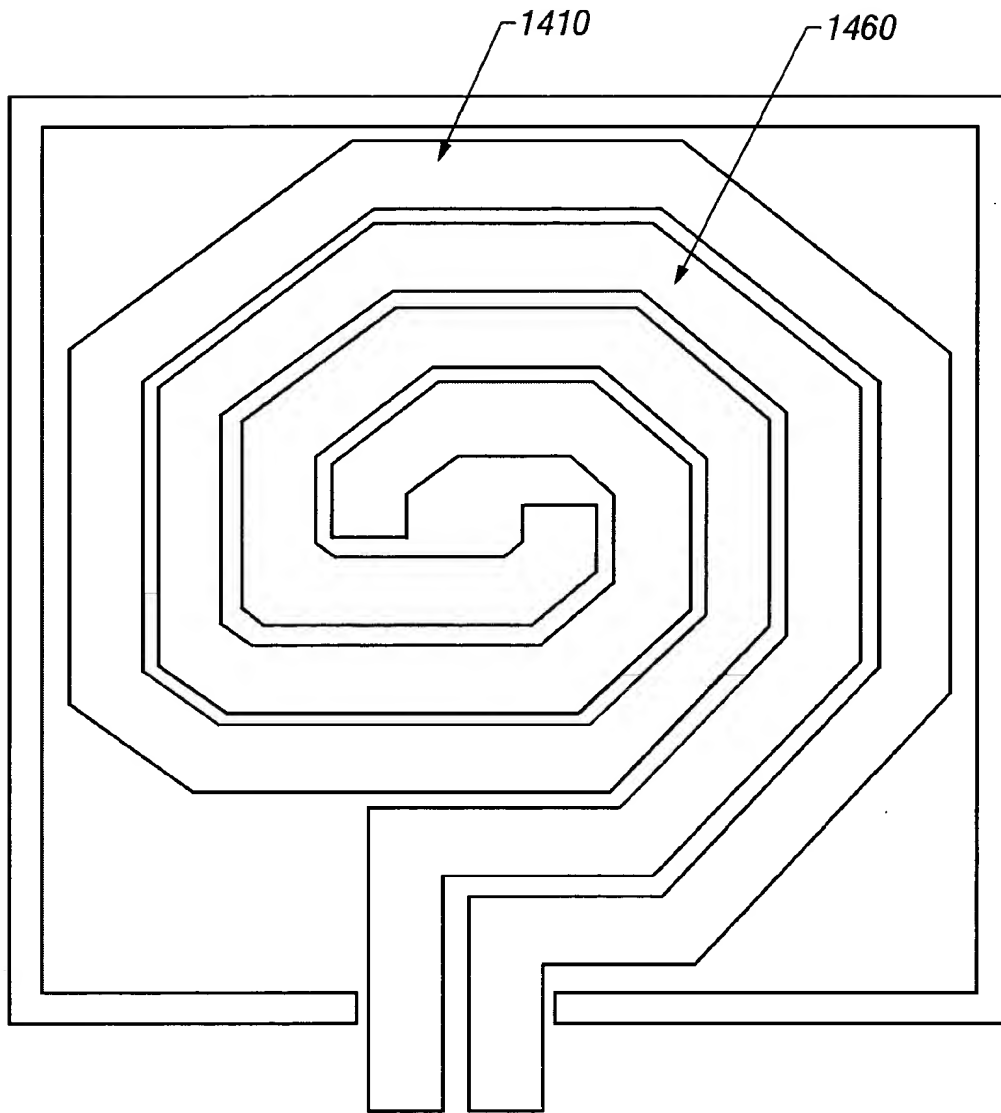


FIG. 14

11/13

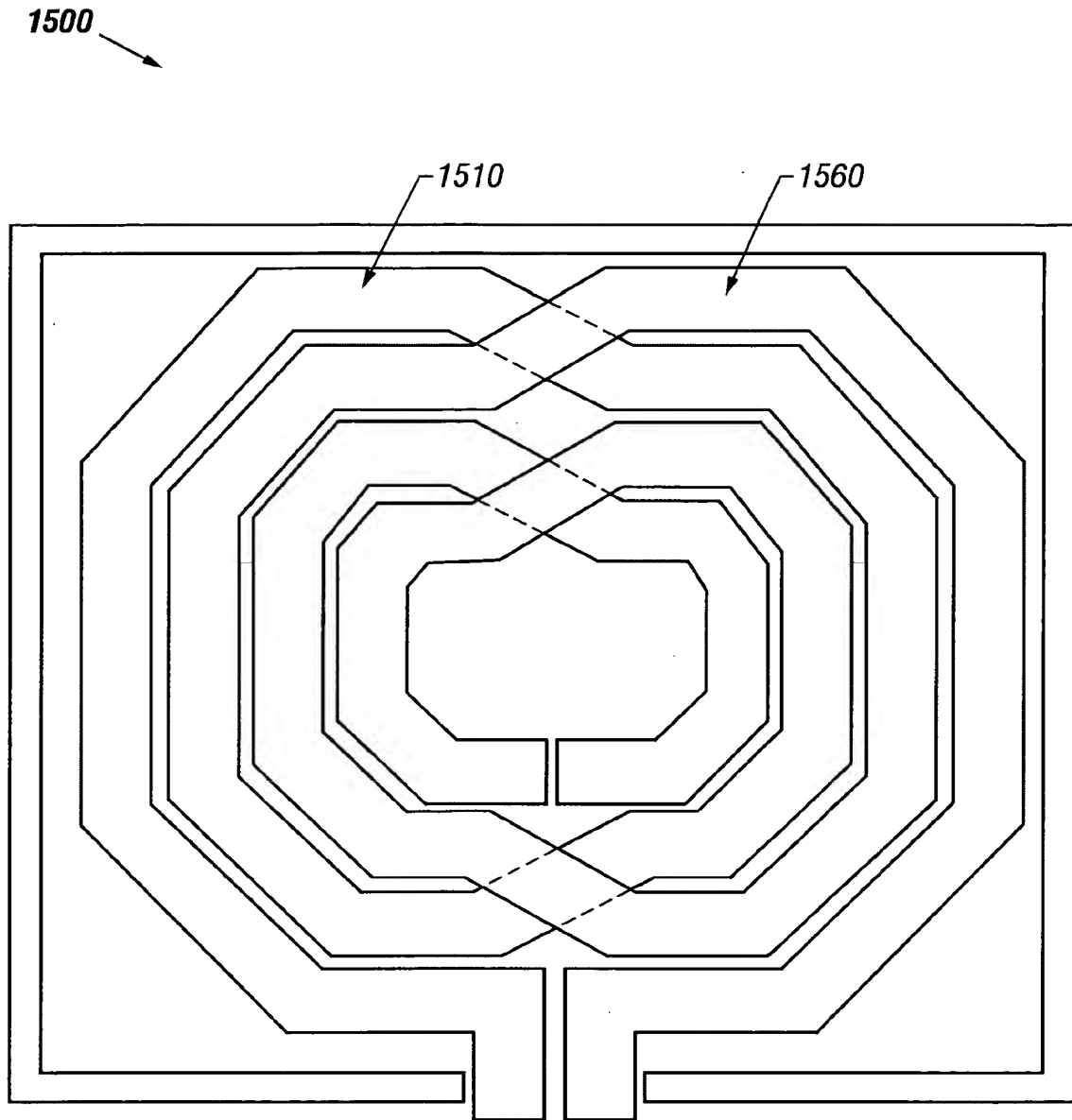
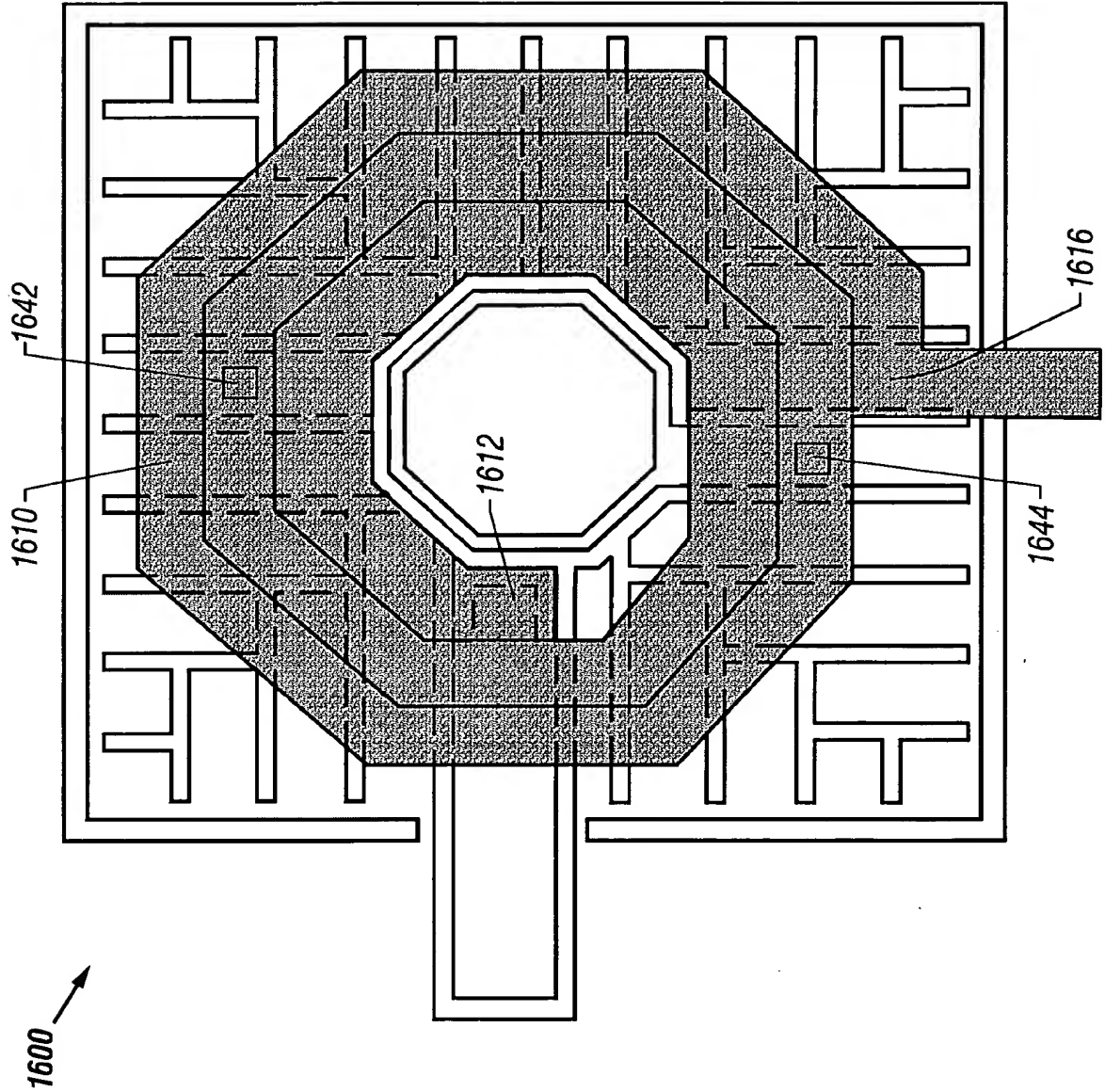


FIG. 15

12/13

FIG. 16



13/13

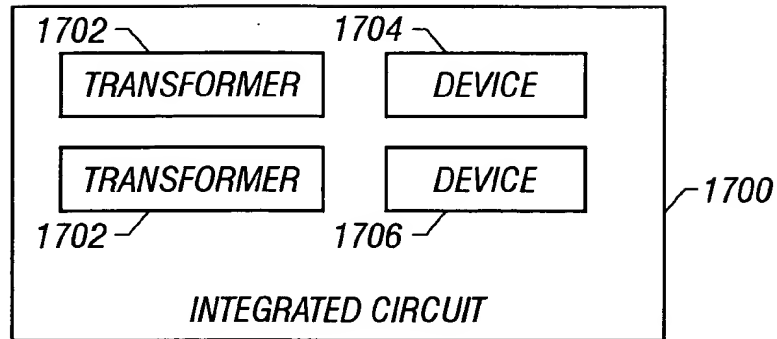


FIG. 17

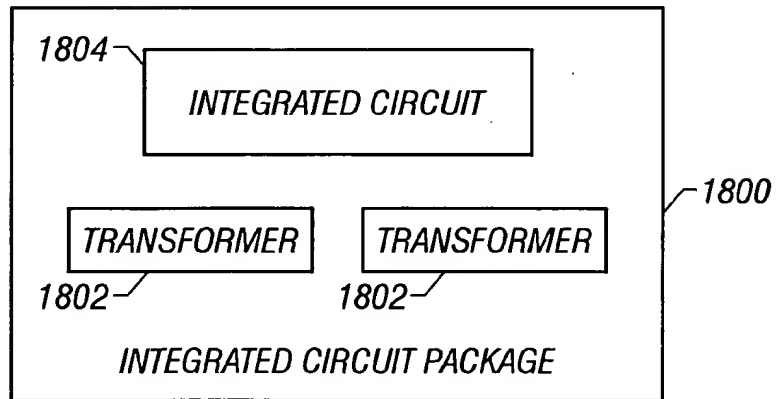


FIG. 18

FIG. 17